Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- · Side wettable flanks for optical solder inspection
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	30	V
V _{GS}	gate-source voltage		-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C	-	-	23	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	-	15	W
Static chara	acteristics		'	'	'	
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 8.4 \text{ A}; T_j = 25 \text{ °C}$	-	13.4	16.8	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain	15776	
3	G	gate		D L
4	S	source	2 5	
5	D	drain	3 8 4	
6	D	drain	Transparent top view	mbb076 S
7	D	drain	DFN2020MD-6 (SOT1220)	
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK6D16-30E		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6D16-30E	M2

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	8.4	Α
		V _{GS} = 10 V; T _{sp} = 25 °C		-	23	Α
		V _{GS} = 10 V; T _{sp} = 100 °C		-	15	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	92	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	2.3	W
		T _{sp} = 25 °C		-	15	W
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-draii	n diode			'		
Is	source current	T _{amb} = 25 °C	[1]	-	2.4	Α
		T _{sp} = 25 °C		-	15	Α
I _{SM}	peak source current	single pulse; $t_p \le 10 \mu s$; $T_{sp} = 25 °C$		-	60	Α
Avalanche r	uggedness		'			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 15.8 A; DUT in avalanche (unclamped)		-	23	mJ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

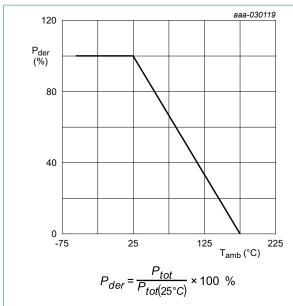


Fig. 1. Normalized total power dissipation as a function of ambient temperature

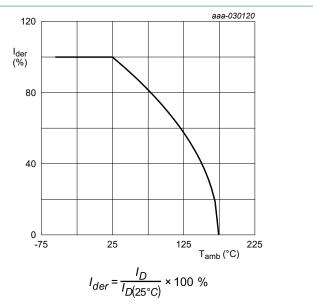


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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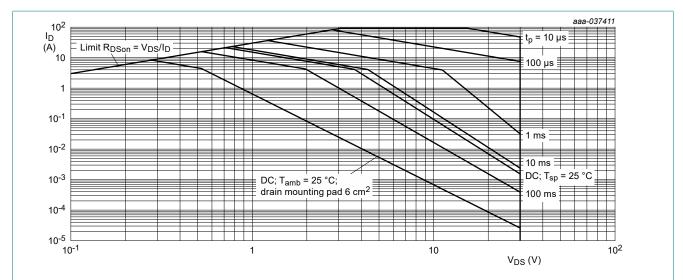


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	57	66	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	7	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

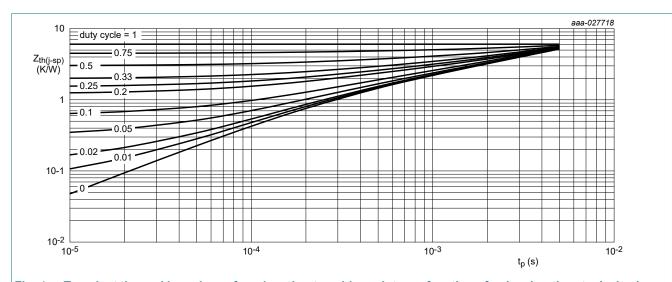


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

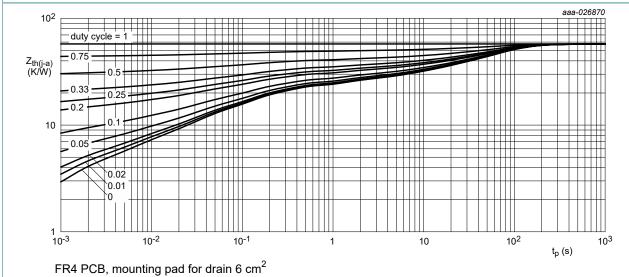


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 8.4 A; T _j = 25 °C	-	13.4	16.8	mΩ
	resistance	V _{GS} = 10 V; I _D = 8.4 A; T _j = 175 °C	-	25	33.3	mΩ
		V _{GS} = 4.5 V; I _D = 6.9 A; T _j = 25 °C	-	17	24.3	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 8.4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	22	-	S
R_G	gate resistance	f = 1 MHz	-	1.8	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 8.4 A; V _{GS} = 10 V;	-	10.7	16	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.5	-	nC
Q_{GD}	gate-drain charge		-	2.3	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	553	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	132	-	pF
C _{rss}	reverse transfer capacitance		-	68	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 8.4 A; V _{GS} = 10 V;	-	2	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time	1	-	12	-	ns
t _f	fall time		-	5	-	ns
Source-drai	in diode		'			
V_{SD}	source-drain voltage	$I_S = 2.4 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 2.4 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	12.1	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	4.2	-	nC

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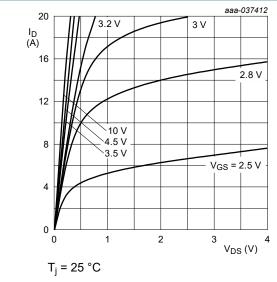


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

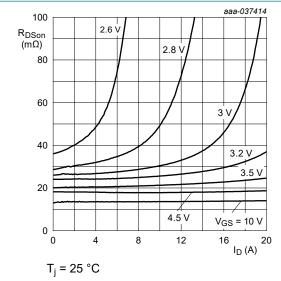


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

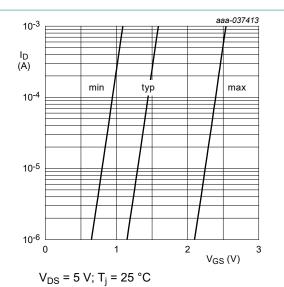


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

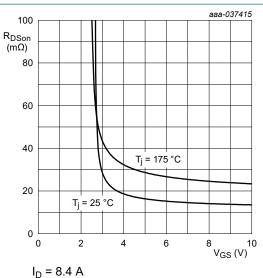


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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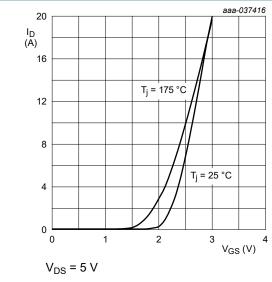


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

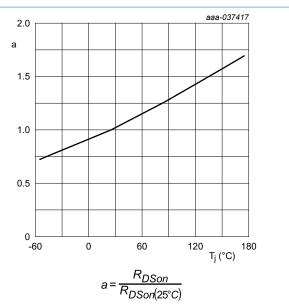


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

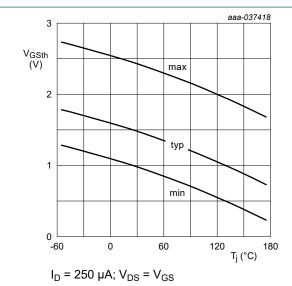
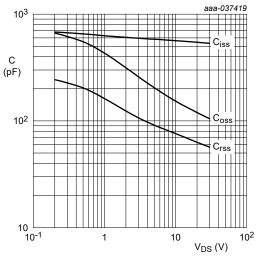


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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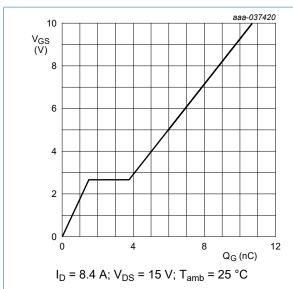


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

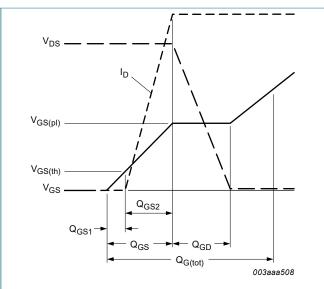


Fig. 15. Gate charge waveform definitions

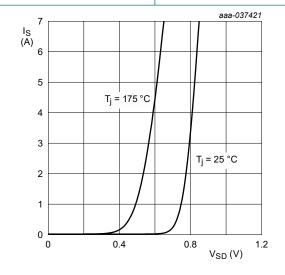
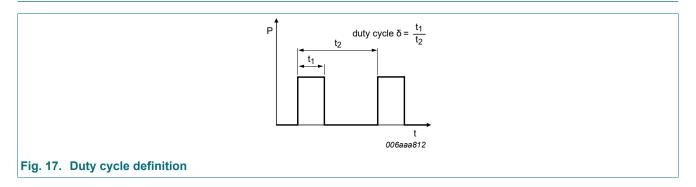


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information

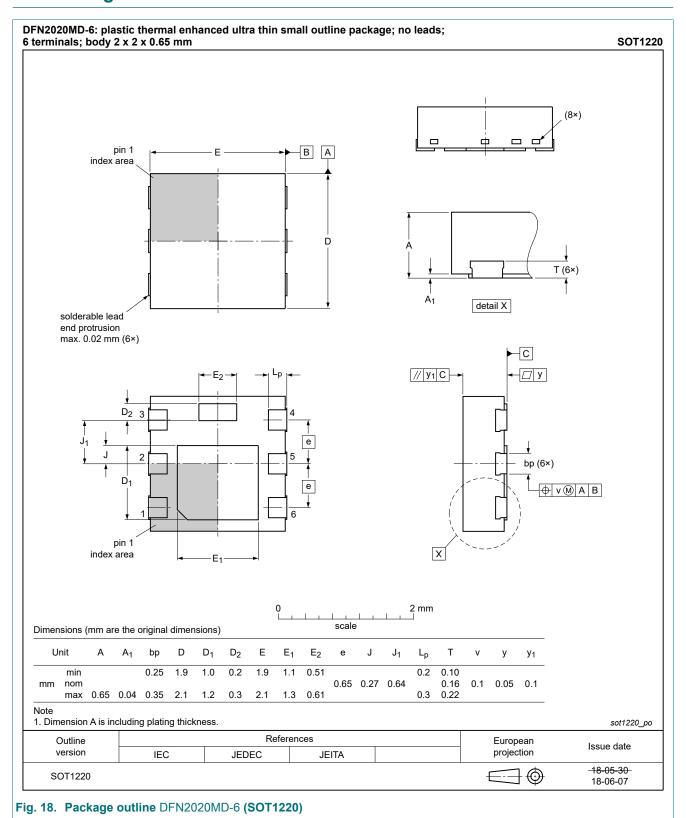


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

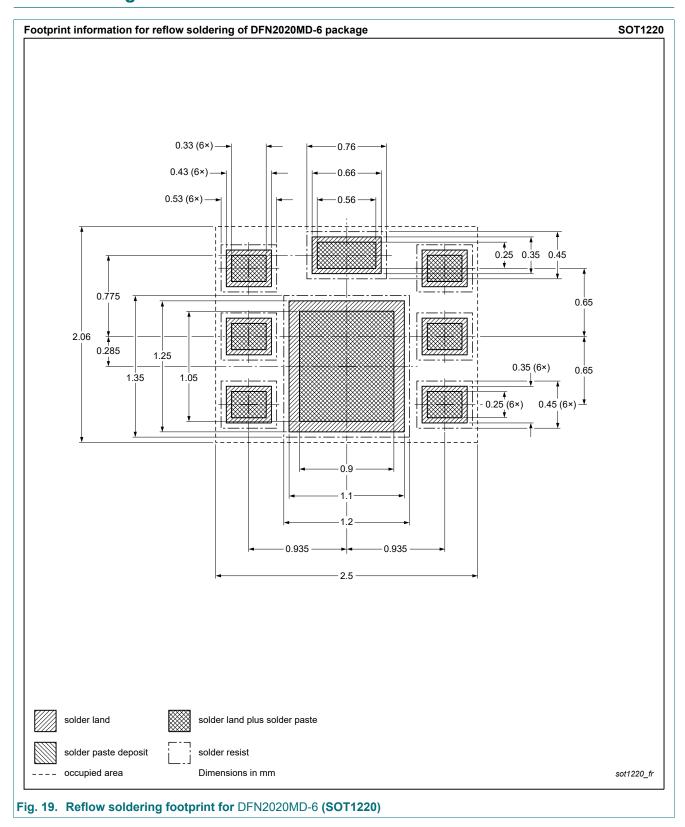
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6D16-30E v.1	20230920	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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